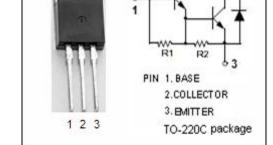


isc Silicon NPN Darlington Power Transistor

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= 120V(Min)
- · High DC Current Gain-
- : h_{FE} = 2000(Min)@ (V_{CE} = 3V, I_{C} = 2A)
- Complement to Type 2SB1339
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

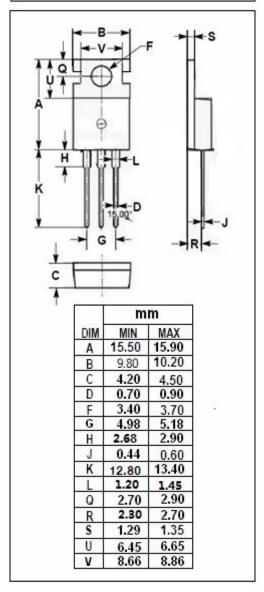


APPLICATIONS

· Designed for power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|----------------------|
| V _{CBO} | Collector-Base Voltage | 120 | V |
| Vceo | Collector-Emitter Voltage | V | |
| V _{EBO} | Emitter-Base Voltage 6 | | V |
| lc | Collector Current-Continuous | 6 | Α |
| Ісм | Collector Current-Peak | 10 | Α |
| Pc | Collector Power Dissipation @T _a =25℃ | 2 | 10/ |
| | Collector Power Dissipation @T _C =25℃ | 40 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ C |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}\mathbb{C}$ |





isc Silicon NPN Darlington Power Transistor

2SD1888

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|------|------|-------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 5mA; I _B = 0 | 120 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 50 μ A; I _E = 0 | 120 | | | V |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = 3A; I _B = 6mA | | | 1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 120V; I _E = 0 | | | 100 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 3 | mA |
| h _{FE} | DC Current Gain | I _C = 2A; V _{CE} = 3V | 2000 | | 20000 | |
| Сов | Output Capacitance | I _E = 0; V _{CB} = 10V; f _{test} = 1MHz | | 50 | | pF |
| f⊤ | Current-Gain—Bandwidth Product | I _E = -0.2A; V _{CE} = 5V; f _{test} = 10MHz | | 40 | | MHz |



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